

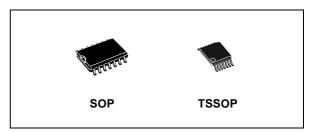
#### DUAL D-TYPE FLIP FLOP WITH PRESET AND CLEAR

- HIGH SPEED: f<sub>MAX</sub> = 160 MHz (TYP.) at V<sub>CC</sub> = 5V
- LOW POWER DISSIPATION:  $I_{CC} = 2 \mu A \text{ (MAX.) at } T_A = 25 ^{\circ}\text{C}$
- COMPATIBLE WITH TTL OUTPUTS: V<sub>IH</sub> = 2V (MIN.), V<sub>IL</sub> = 0.8V (MAX)
- POWER DOWN PROTECTION ON INPUTS & OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE: |I<sub>OH</sub>| = I<sub>OL</sub> = 8 mA (MIN)
- BALANCED PROPAGATION DELAYS: tplh ≅ tphl
- OPERATING VOLTAGE RANGE: V<sub>CC</sub>(OPR) = 4.5V to 5.5V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 74
- IMPROVED LATCH-UP IMMUNITY

#### **DESCRIPTION**

The 74VHCT74A is an advanced high-speed CMOS DUAL D-TYPE FLIP FLOP WITH PRESET AND CLEAR fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

A signal on the D INPUT is transferred to the Q OUTPUT during the positive going transition of the clock pulse.



**Table 1: Order Codes** 

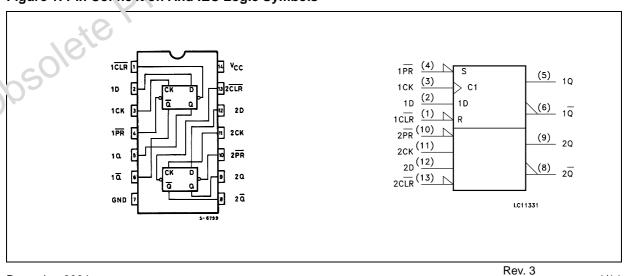
PACKAGE	T & R
SOP	74VHCT/4AMTR
TSSOP	7 1V ICT74ATTR

CLR and PR are independent of the clock and accomplished by a row setting on the appropriate input.

Power c'c vn protection is provided on all inputs and outputs and 0 to 7V can be accepted on incut; with no regard to the supply voltage. This device can be used to interface 5V to 3V since all inputs are equipped with TTL threshold.

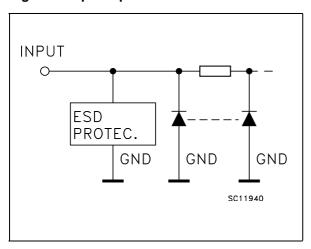
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

Figure 1: Pin Conne nion And IEC Logic Symbols



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Figure 2: Input Equivalent Circuit



**Table 2: Pin Description** 

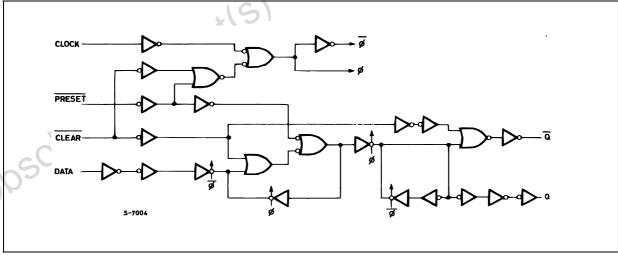
PIN N°	SYMBOL	NAME AND FUNCTION
1, 13	1CLR, 2CLR	Asynchronous Reset - Direct Input
2, 12	1D, 2D	Data Inputs
3, 11	1CK, 2CK	Clock Input (LOW to HIGH, Edge Triggered)
4, 10	1PR, 2PR	Asynchronous Set - Direct Input
5, 9	1Q, 2Q	True Flip-Flop Outputs
6, 8	1Q, 2Q	Complement Flip-Flop Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

**Table 3: Truth Table** 

	INP	JTS		ОИТІ	PUTS	FUNCTION		
CLR	PR	D	СК	Q	Q	FUNCTION		
L	Н	Х	Х	L	Н	CLEAR		
Н	L	X	X	Н	Ð	PRESET		
L	L	X	X	Н	Н			
Н	Н	L		L	KOH			
Н	Н	Н		Н	L			
Н	Н	Х	L	$Q_{n}$	$\overline{Q}_n$	NO CHANGE		

X : Don't Care

Figure 3: Logic Diagram



This logic diagram has not be used to estimate propagation delays

**Table 4: Absolute Maximum Ratings** 

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 1)	-0.5 to +7.0	V
Vo	DC Output Voltage (see note 2)	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

1)  $V_{CC} = 0V$ 2) High or Low State

**Table 5: Recommended Operating Conditions** 

	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage (see note 1)	0 to 5.5	V
Vo	Output Voltage (see note 2)	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (see note 3) $(V_{CC} = 5.0 \pm 0.5V)$	0 to 20	ns/V
	y State By to 2V		



**Table 6: DC Specifications** 

		1	est Condition				Value				
Symbol	Parameter	V <sub>CC</sub>		Т	T <sub>A</sub> = 25°C -4			-40 to 85°C		-55 to 125°C	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input Voltage	4.5 to 5.5		2			2		2		V
V <sub>IL</sub>	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V <sub>OH</sub>	High Level Output	4.5	I <sub>O</sub> =-50 μA	4.4	4.5		4.4		4.4		V
	Voltage	4.5	I <sub>O</sub> =-8 mA	3.94			3.8		3.7		V
V <sub>OL</sub>	Low Level Output	4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	V
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1.0		± 1.0	μΑ
Icc	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			2		20		20	μΑ
+I <sub>CC</sub>	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V <sub>CC</sub> or GND			1.35		1.5	UC,	1.5	mA
I <sub>OPD</sub>	Output Leakage Current	0	V <sub>OUT</sub> = 5.5V			0.5	20	5.0	•	5.0	μΑ

**Table 7: AC Electrical Characteristics** (Input  $t_r = t_f = 3ns$ )

		1	est C	ondition		7/6	3	Value				
Symbol	Parameter	v <sub>cc</sub>	CL		Œ	T <sub>A</sub> = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)	(pF)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t <sub>PLH</sub>	Propagation Delay	5.0 <sup>(*)</sup>	15			5.8	7.8	1.0	9.0	1.0	9.0	ns
t <sub>PHL</sub>	Time CK to Q or Q	5.0 <sup>(*)</sup>	50	<b>S</b>		6.3	8.8	1.0	10.0	1.0	10.0	115
t <sub>PLH</sub>	Propagation Delay	5.0 <sup>(*)</sup>	15	5		7.6	10.4	1.0	12.0	1.0	12.0	
t <sub>PHL</sub>	Time PR or CLR to Q or Q	5.0 <sup>(*)</sup>	50			8.1	11.4	1.0	13.0	1.0	13.0	ns
t <sub>W</sub>	CK Pulse Width HIGH or LOW	5.0 <sup>(*)</sup>					5.0		5.0		5.0	ns
t <sub>W</sub>	PR or CLR Pulse Width LOW	5.0 <sup>(*)</sup>					5.0		5.0		5.0	ns
t <sub>s</sub>	Setup Time D to CK HIGH or LOW	5.0 <sup>(*)</sup>					5.0		5.0		5.0	ns
t <sub>h</sub>	Hold Time D to CK HIGH or LOW	5.0 <sup>(*)</sup>					0.0		0.0		0.0	ns
t <sub>REM</sub>	Removal Time PR or CLR to CK	5.0 <sup>(*)</sup>					3.5		3.5		3.5	ns
f <sub>MAX</sub>	Maximum Clock	5.0 <sup>(*)</sup>	15		100	160		80		80		MHz
	Frequency	5.0 <sup>(*)</sup>	50		80	140		65		65		IVIITZ

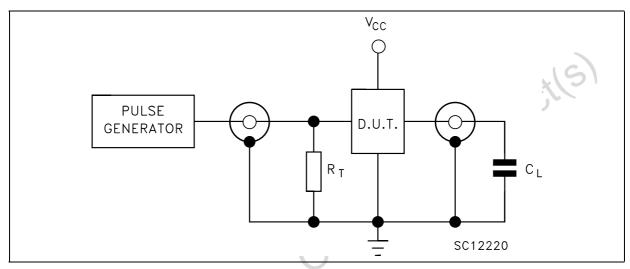
<sup>(\*)</sup> Voltage range is  $5.0\text{V} \pm 0.5\text{V}$ 

**Table 8: Capacitive Characteristics** 

		Test Condition		Value						
Symbol	Parameter		T <sub>A</sub> = 25°C -40 to 85°C -55 to 1		125°C	Unit				
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance			6	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)			21						pF

<sup>1)</sup>  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$  (per gate)

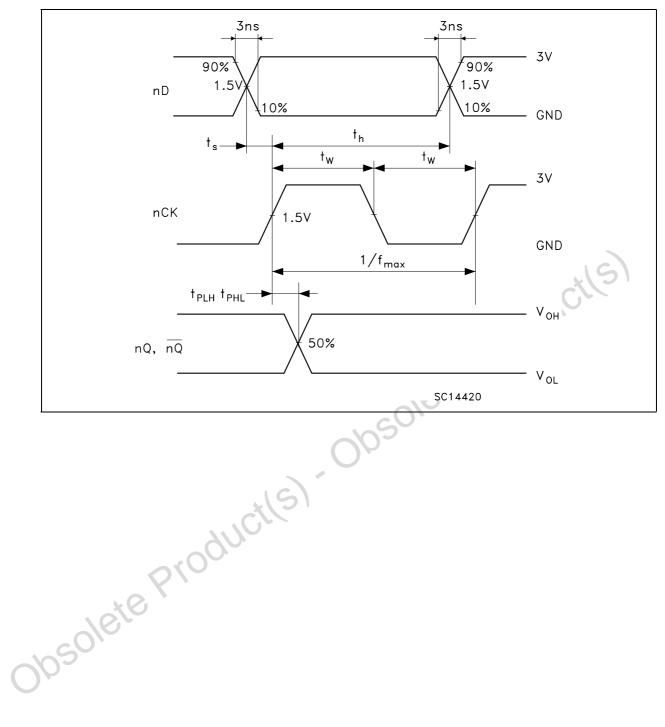
Figure 4: Test Circuit



Obsolete Produciles  $C_L$  =15/50pF or equivalent (includes jig and probe capacitance)  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega)$ 

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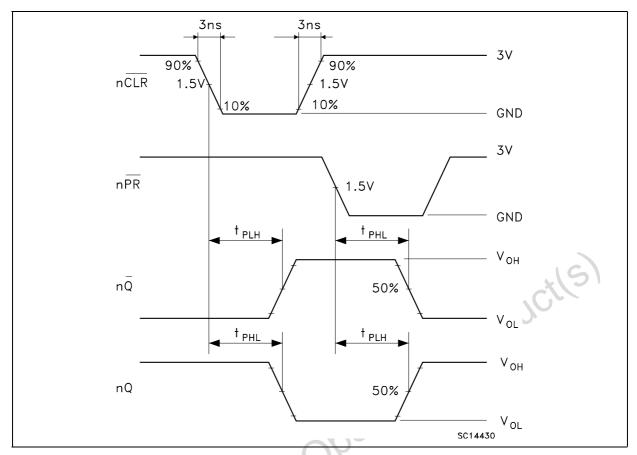


Figure 6: Waveform - Propagation Delays (f=1MHz; 50% duty cycle)



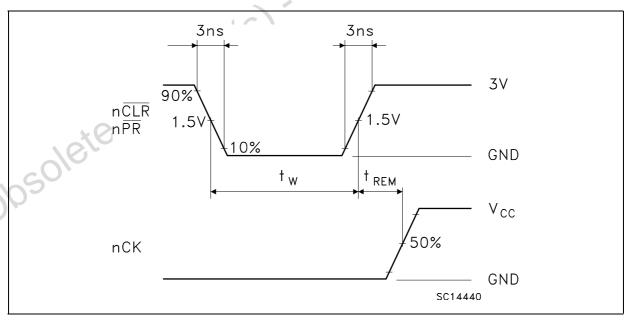
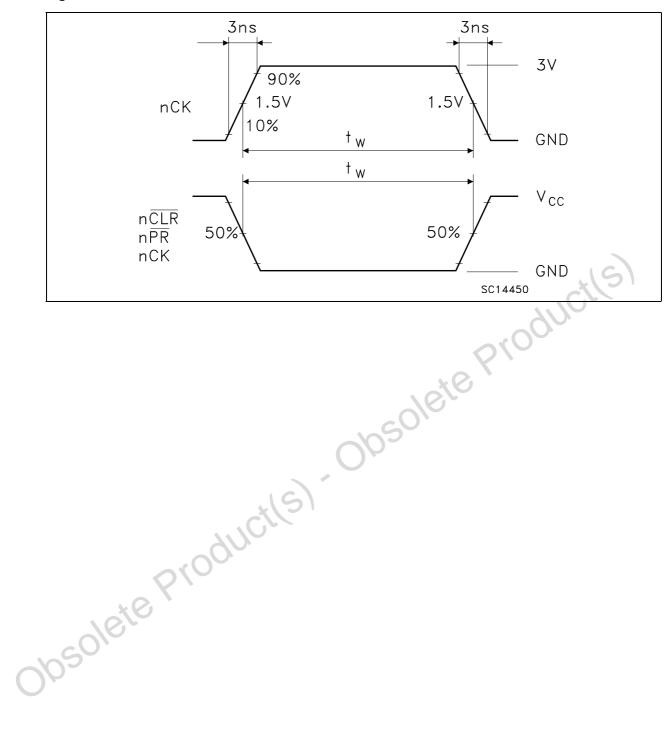
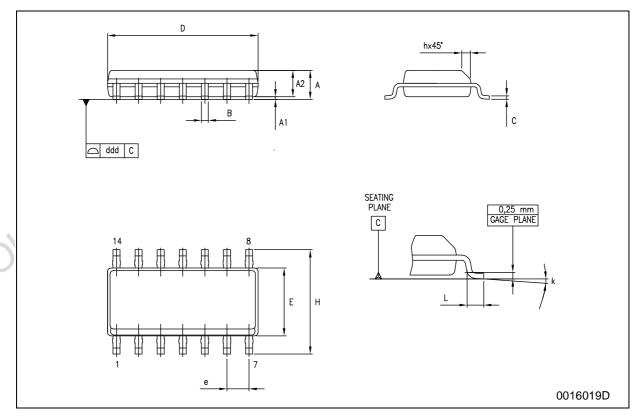


Figure 8: Waveform - Pulse Width



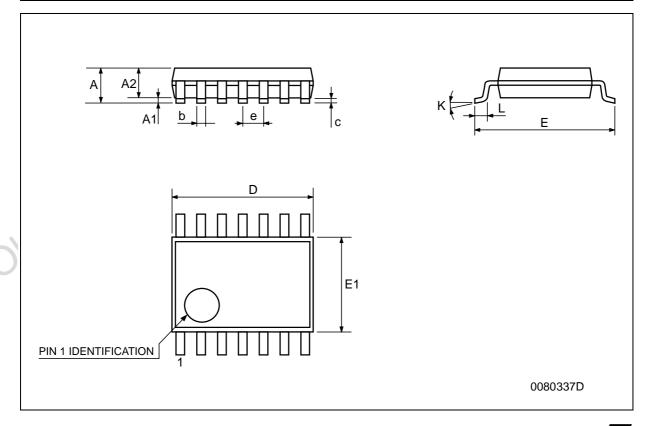
### **SO-14 MECHANICAL DATA**

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А	1.35		1.75	0.053		0.069		
A1	0.1		0.25	0.004		0.010		
A2	1.10		1.65	0.043		0.065		
В	0.33		0.51	0.013		0.020		
С	0.19		0.25	0.007		0.010		
D	8.55		8.75	0.337		0.344		
Е	3.8		4.0	0.150		0.157		
е		1.27			0.050			
Н	5.8		6.2	0.228		0.244		
h	0.25		0.50	0.010		0.020		
L	0.4		1.27	0.016		0.050		
k	0°		8°	0°		8°		
ddd			0.100			0.004		



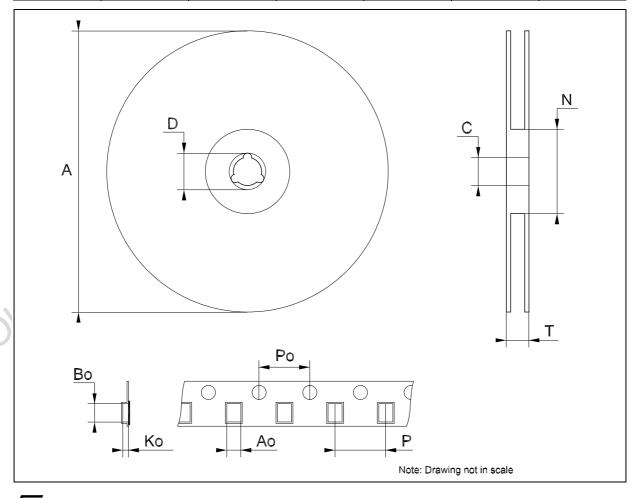
### **TSSOP14 MECHANICAL DATA**

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			1.2			0.047	
A1	0.05		0.15	0.002	0.004	0.006	
A2	0.8	1	1.05	0.031	0.039	0.041	
b	0.19		0.30	0.007		0.012	
С	0.09		0.20	0.004		0.0089	
D	4.9	5	5.1	0.193	0.197	0.201	
E	6.2	6.4	6.6	0.244	0.252	0.260	
E1	4.3	4.4	4.48	0.169	0.173	0.176	
е		0.65 BSC			0.0256 BSC		
К	0°		8°	0°		8°	
L	0.45	0.60	0.75	0.018	0.024	0.030	



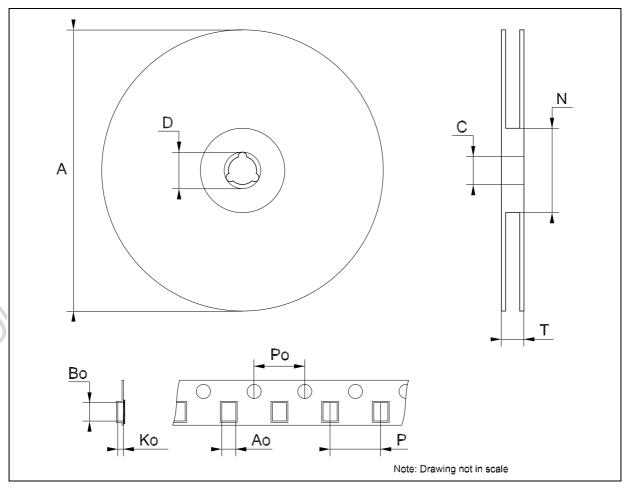
# Tape & Reel SO-14 MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			330			12.992	
С	12.8		13.2	0.504		0.519	
D	20.2			0.795			
N	60			2.362			
Т			22.4			0.882	
Ao	6.4		6.6	0.252		0.260	
Во	9		9.2	0.354		0.362	
Ko	2.1		2.3	0.082		0.090	
Po	3.9		4.1	0.153		0.161	
Р	7.9		8.1	0.311		0.319	



# Tape & Reel TSSOP14 MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α			330			12.992	
С	12.8		13.2	0.504		0.519	
D	20.2			0.795			
N	60			2.362			
Т			22.4			0.882	
Ao	6.7		6.9	0.264		0.272	
Во	5.3		5.5	0.209		0.217	
Ko	1.6		1.8	0.063		0.071	
Po	3.9		4.1	0.153		0.161	
Р	7.9		8.1	0.311		0.319	



**Table 9: Revision History** 

Date	Revision	Description of Changes
16-Dec-2004	3	Order Codes Revision - pag. 1.



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